

Photomask Blank

ABSTRACT

5 A photomask blank comprising a transparent substrate
and a chromium-containing film deposited thereon is provided.
The chromium-containing film comprises at least one CrC
compound layer comprising up to 50 at% of Cr, at least 25 at%
of O and/or N, and at least 5 at% of C. From the blank, a
photomask having a photomask pattern formed on the substrate
10 is produced, the photomask being used in photolithography of
forming a resist pattern with a line width of up to 0.1 μm ,
using exposure light having a wavelength of up to 250 nm.

[Fig. 1]